



Frontier Electronics Corp.

667 E. COCHRAN STREET, SIMI VALLEY, CA 93065

TEL: (805) 522-9998 FAX: (805) 522-9989

E-mail: frontiersales@frontierusa.com

Web: <http://www.frontierusa.com>

SUPER SWITCHING CHIP DIODE

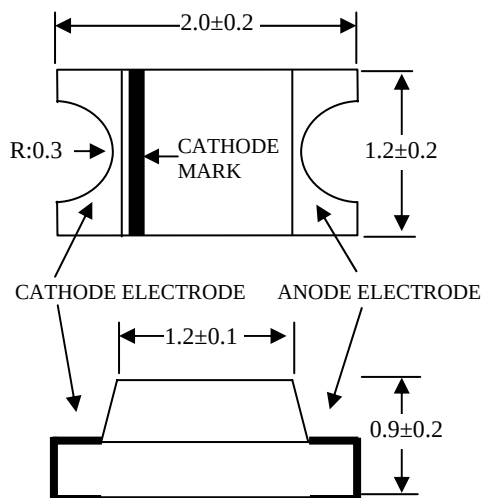
SSD355

FEATURES

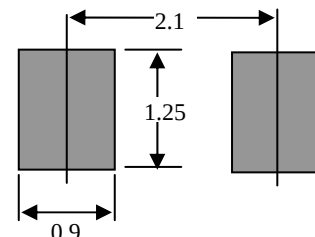
- SUPER SWITCHING
- CHIP DIODE SIZE
- LOW STORED CHARGE

MECHANICAL DATA

- CASE: SOD-323, MINI MELF, DIMENSIONS IN MILLIMETERS
- TERMINALS: SOLDERABLE PER MIL-STD 750 METHOD 2026
- POLARITY: CATHODE INDICATED BY COLOR BAND



Recommended Land Pattern Dimensions



RATINGS	SYMBOL	SSD355	UNITS
CONTINUOUS REVERSE VOLTAGE	V_R	100	V
RECTIFIED CURRENT (AVERAGE) HALF WAVE RECTIFICATION WITH RESIST LOAD AT $T_{amb} = 25^{\circ}\text{C}$ AND $f \geq 50\text{HZ}$ (NOTE 1)	I_O	100	mA
SURGE FORWARD CURRENT AT $T < 1\text{ s}$ AND $T_J = 25^{\circ}\text{C}$	I_{FSM}	500	mA
POWER DISSIPATION AT $T_{amb}=25^{\circ}\text{C}$	P_{TOT}	350	mW
JUNCTION TEMPERATURE	T_J	175	$^{\circ}\text{C}$
STORAGE TEMPERATURE RANGE	T_S	- 55 TO + 175	$^{\circ}\text{C}$

CHARACTERISTICS $T_J=25^{\circ}\text{C}$	SYMBOL	MIN	TYP	MAX	UNITS
FORWARD VOLTAGE AT $I_F=100\text{mA}$	V_F	-	-	1	V
LEAKAGE CURRENT AT $V_R=25\text{V}$	I_R	-	-	30	nA
AT $V_R=80\text{V}$	I_R	-	-	0.1	μA
REVERSE BREAKDOWN VOLTAGE TESTED WITH $100\mu\text{A}$ PULSES	V_R	100	-	-	V
CAPACITANCE AT $V_F=V_R=0$, $f = 1.0\text{ MHz}$	C_D	-	-	1.5	PF
REVERSE RECOVERY TIME FROM $I_F=10\text{mA}$ TO $I_R=1\text{mA}$ $V_R=6\text{V}$ $R_L=100\Omega$	T_{RR}	-	-	4	nS
THERMAL RESISTANCE JUNCTION TO AMBIENT AIR (NOTE 1)	R_{THA}	-	-	0.35	K / mW

NOTE: 1. LEADS KEPT AT AMBIENT TEMP.

RATINGS AND CHARACTERISTIC CURVE SSD355

Fig. 1-REVERSE CHARACTERISTICS

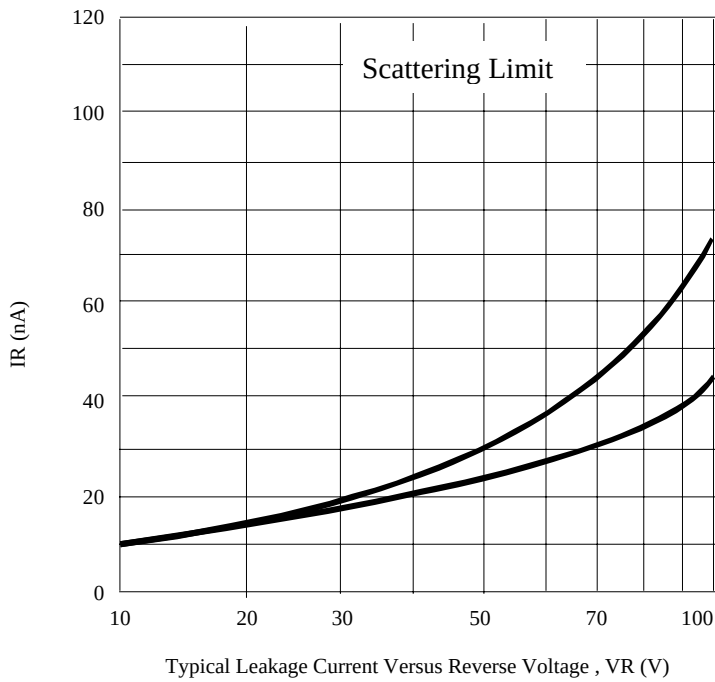
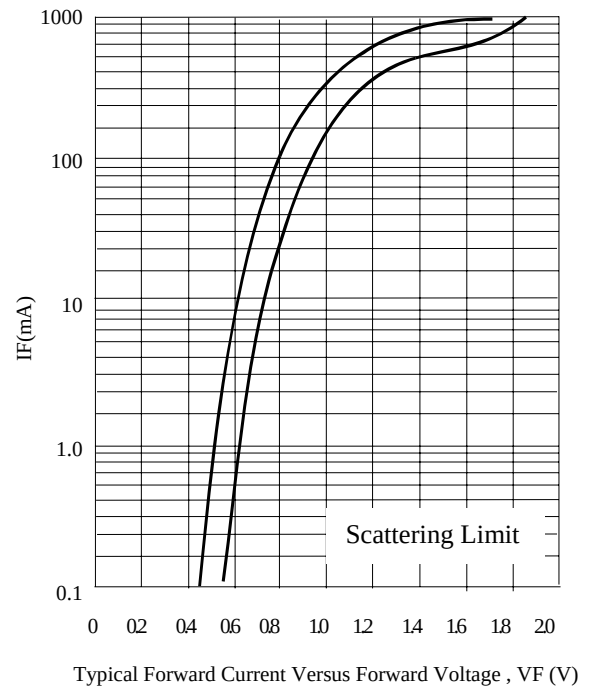


Fig. 2-FORWARD CHARACTERISTICS



ODES CAPACITANCE

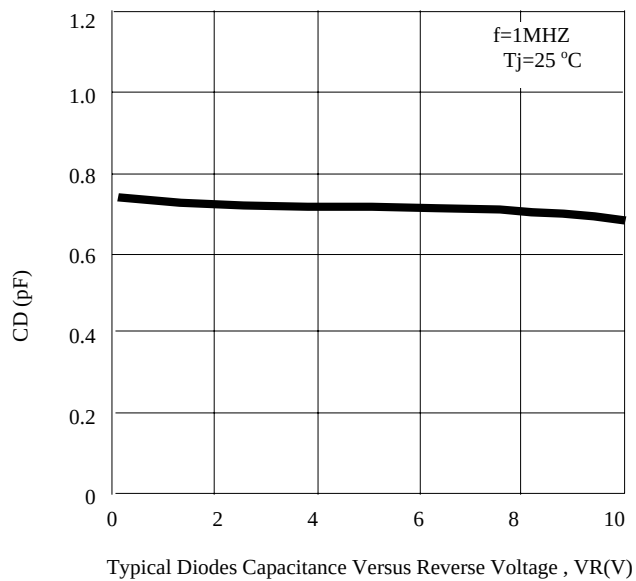


Fig. 4-DERATING CURVE

